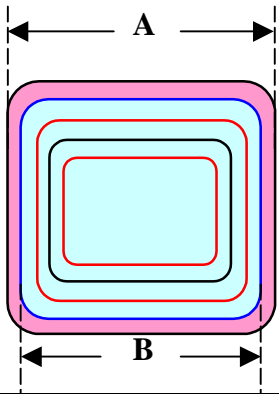


<b>Features :</b>  <ul style="list-style-type: none"> <li>* Extremely low forward volts</li> <li>* Guard ring protection</li> <li>* Low reverse leakage current</li> </ul> 	Chip size(A):	1.524* 1.524 mm <sup>2</sup>	
	Bond Pad size(B) :	1.422 *1.422 mm <sup>2</sup>	
	Thickness :	300μm ± 20μm	
	Metalization :	Anode Ti/Ni/Ag	
	Metalization :	Cathode Ti/Ni/Ag	
Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 3.0Amp. 25°C	VF max	0.70	Volt
Minimum Instantaneous Reverse Voltage at IR : 300 uA 25°C	VR min.	63	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	80	Amp
Storage Temperature	TSTG	-65 to +125	°C

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